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REQUEST . .?

NTINUED EXAMINATION (RCE) TRANSMITTAL

Subsection (b) of 35 U.S.C. § 132, effective on May 29, 2000, provides for continued examination of an utility or plant application filed on or after June 8, 1995.

See The American Inventors Protection Act of 1999 (AIPA).

Application Number	10/602,315
Filing Date	June 24, 2003
First Named Inventor	Kie Y. Ahn
Group Art Unit	2829
Examiner Name	Asok K. Sarkar
Attorney Docket Number	1303.107US1
Customer No.	21186

This is a Request for Continued Examination (RCE) under 37 CFR § 1.114 of the above-identified application entitled LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS.

Submission required under 37 C.F.R. § 1.114

- 1. _ Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on .
- 2. _ Consider the arguments in the Appeal Brief or Reply Brief previously filed on .
- 3. _ An Amendment Under 37 CFR § 1.116 (pages) is enclosed.
- 4. _ A new power of attorney (pages) is enclosed.
- 5. \underline{X} An Information Disclosure Statement is enclosed (2 pages).
 - a. 1 Form(s) 1449
 - b. 9 Copies of IDS Citations
- 6. X A check in the amount of \$790.00 is attached to pay the RCE filing fee required under C.F.R. § 1.17(e).
- 7. X The Commissioner is hereby authorized to credit overpayments or charge any fees set forth in 37 CFR §§ 1.16 through 1.18 to Deposit Account No. 19-0743.
- 8. _ A Petition for Extension of Time in the prior application (pages) is enclosed along with a check in the amount of to pay the extension fee.
- 9. X Others: Communication Concerning Related Applications (2 pgs.).

SCHWEGMAN,	LUNDBERG,	WOESSNER	&	KLUTH,	P.A.

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Atty: David R. Cochran

Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Attn-Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this ____ day of March, 2005.

KACIA LEE

Kacia Lee

Name

<u>N 10/602,315</u> <u>PATENT</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1 4 200 Applicant:

Kie Y. Ahn et al.

Examiner: Asok K. Sarkar

al No.:

10/602,315

Group Art Unit: 2829

fled:

June 24, 2003

Docket: 1303.107US1

Title:

LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No. 11/036296	Filing Date January 14, 2005	Attorney Docket 1303.030US2	Title LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/909959	August 2, 2004	1303.114US1	ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS
10/931533	August 31, 2004	1303.119US1	ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS
10/926812	August 26, 2004	1303.121US1	RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER
10/930167	August 31, 2004	1303.122US1	ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER
11/010529	December 13, 2004	1303.126US1	ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS
11/029757	January 5, 2005	1303.127US1	ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/602,315 Filing Date: June 24, 2003

Title: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

Page 2 Dkt: 1303.107US1

11/010766 December 1303.129US1 HYBRID ALD-CVD OF PrXOY/ZrO2 FILMS AS GATE DIELECTRICS 11/053577 February 8, 2005 Pebruary 8, 2005 ATOMIC LAYER DEPOSITION OF DYDOPED HFO2 FILMS AS GATE DIELECTRICS 11/058563 February 1303.133US1 ATOMIC LAYER DEPOSITION OF Zr3N4/ZrO2 FILMS AS GATE DIELECTRICS February 1303.134US1 ATOMIC LAYER DEPOSITION OF Hf3N4/Hf02 FILMS AS GATE DIELECTRICS 11/031289 January 7, 2005 LANTHANIDE DOPED TIOX DIELECTRIC FILMS BY PLASMA OXIDATION 11/059594 February 1303.046US2 EVAPORATED LaAIO3 FILMS FOR GATE DIELECTRICS	Title. EXITTIANDE OF	AIDE/ HAI MOW OX	IDE DIEEECTRICS	
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15, 2005 February 1303.134US1 ATOMIC LAYER DEPOSITION OF Hf3N4/Hf02 FILMS AS GATE DIELECTRICS 11/031289 January 7, 1303.069US3 LANTHANIDE DOPED TIOX DIELECTRIC FILMS BY PLASMA OXIDATION 11/059594 February 1303.046US2 EVAPORATED LaAIO3 FILMS FOR	11/053577	•	1303.131US1	DOPED HFO2 FILMS AS GATE
23, 2005 Hf3N4/Hf02 FILMS AS GATE DIELECTRICS 11/031289 January 7, 1303.069US3 LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION 11/059594 February 1303.046US2 EVAPORATED LaAlO3 FILMS FOR	11/058563	•	1303.133US1	Zr3N4/ZrO2 FILMS AS GATE
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2 The Old 12 Day 100 The Old 12	11/031289	• .	1303.069US3	DIELECTRIC FILMS BY PLASMA
	11/059594	-	1303.046US2	

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this day of March, 2005. Vacia Lee Signature